inverting input of this operational amplifier and to a first main electrode of this transistor, wherein one end of said second resistor is connected to the first control signal voltage and the other end of said second resistor is connected to a second main electrode of this transistor which provides the second control signal, and wherein the output of this operational amplifier is connected to a control electrode of this transistor.

7. (amended) A device as claimed in claim 5, wherein the comparison means includes an operational amplifier, wherein a non-inverting input of this operational amplifier is connected to the current limit defining reference voltage, wherein an inverting input of this operational amplifier is connected to the voltage across the current sensing resistance, and wherein the output of this operational amplifier provides the first control signal.

8. (amended) A device as claimed in claim 1, wherein the main transistor section comprises a power MOSFET or IGBT.

9. (amended) A device as claimed in claim 1, wherein, within an encapsulation for the device, the main transistor section, the sense transistor section, the control means and the further control means are provided as a single integrated circuit chip.